



SSC8152GS9

N-Channel Enhancement Mode MOSFET with ESD Protection

➤ Features

V _{DS}	V _{GS}	R _{DS(ON)} Typ.	I _D	ESD
50V	±12V	0.9Ω@10V	0.55A	500V
		1Ω@4V5		

➤ Description

This device is an N-Channel enhancement mode MOSFET, with low on-resistance, fast switching speed and low threshold voltage, it is ideal for portable equipment. and thin outline saves PCB consumption.

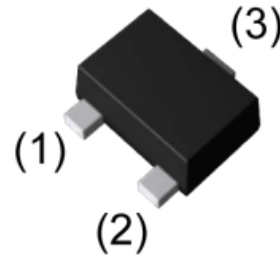
➤ Applications

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers
- Display, Memories, Transistors, etc.
- Battery Operated System
- Solid-State Relays

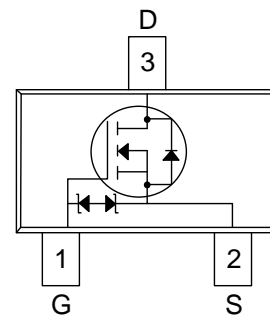
➤ Ordering Information

Device	Package	Shipping
SSC8152GS9	SOT-723	8000/Reel

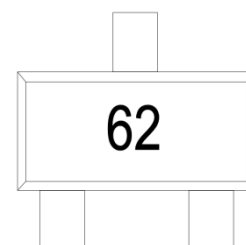
➤ Pin configuration



SOT-723



Pin Configuration (Top View)



Marking



➤ **Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Unit
V_{DS}	Drain-to-Source Voltage	50	V
V_{GS}	Gate-to-Source Voltage	± 12	V
I_D	Continuous Drain Current ^a	0.55	A
I_{DM}	Pulsed Drain Current ^b	2.2	A
P_D	Power Dissipation ^c	0.5	W
T_J	Operation junction temperature	-55~150	$^{\circ}\text{C}$
T_{STG}	Storage temperature range	-55~150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	280	360	$^{\circ}\text{C}/\text{W}$

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(\text{MAX})}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

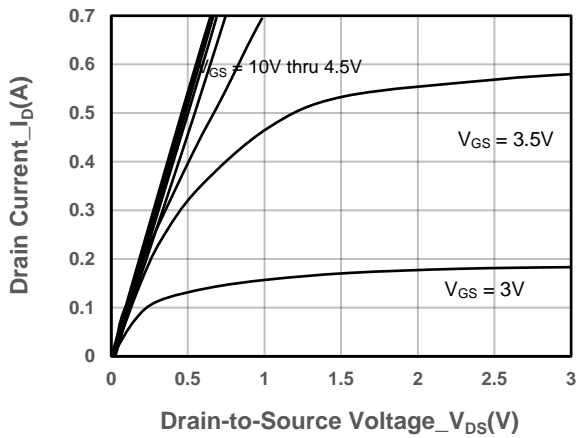


➤ **Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

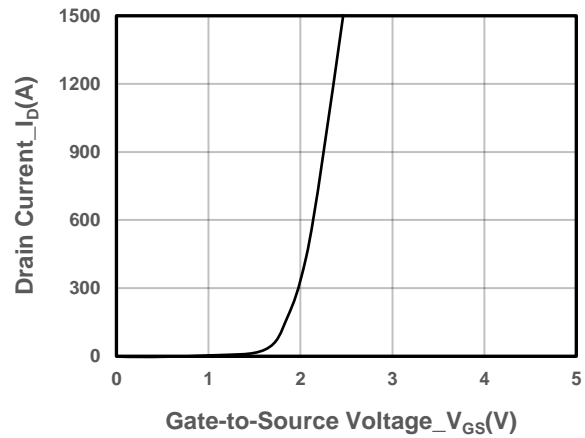
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	50			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.75	1	1.25	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5A$		0.9	2	Ω
		$V_{GS} = 4.5V, I_D = 0.5A$		1	3	
		$V_{GS} = 2.5V, I_D = 0.2A$		1.2	3.5	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50V, V_{GS} = 0V$			1	μA
Gate-Source Leak Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 10	μA
Transconductance	G_{FS}	$V_{DS} = 10V, I_D = 0.2A$		0.1		s
Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 0.2A$			1.3	V
Input Capacitance	C_{ISS}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1MHz$		30		pF
Output Capacitance	C_{OSS}			5.3		
Reverse Transfer Capacitance	C_{RSS}			3		
Turn-on Delay Time	$T_{D(ON)}$	$V_{GS} = 10V, V_{DS} = 10V,$ $I_D = 0.1A$		24		ns
Rise Time	T_r			10		
Turn-off Delay Time	$T_{D(OFF)}$			37		
Fall Time	T_f			21		
Total Gate Charge	Q_G	$V_{GS} = 10V, V_{DS} = 15V$ $I_D = 0.2A$		0.42		nC
Gate to Source Charge	Q_{GS}			0.1		
Gate to Drain Charge	Q_{GD}			0.12		



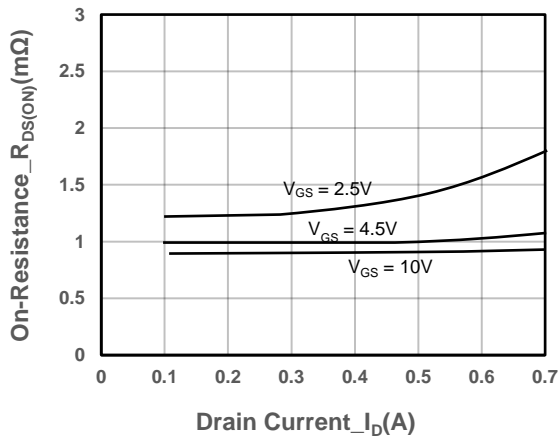
➤ Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)



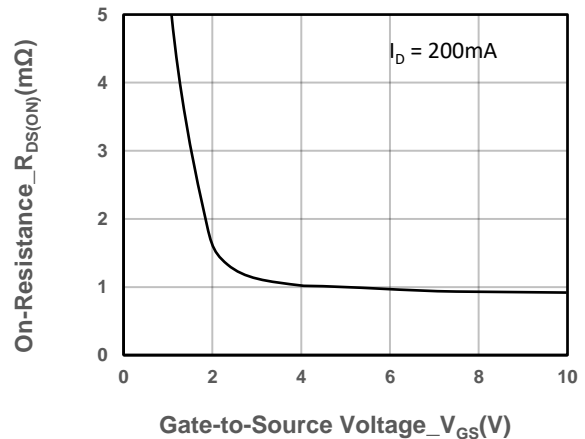
Output Characteristics



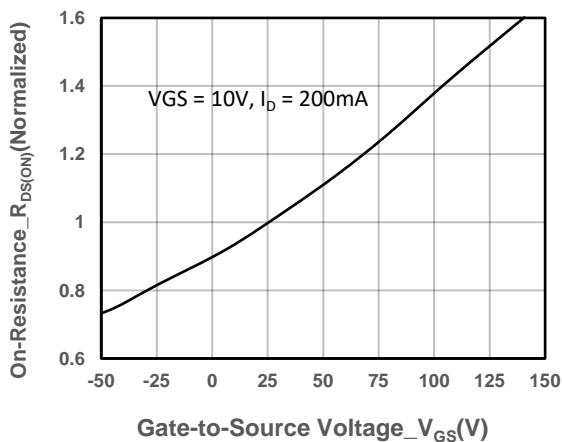
Transfer Characteristics



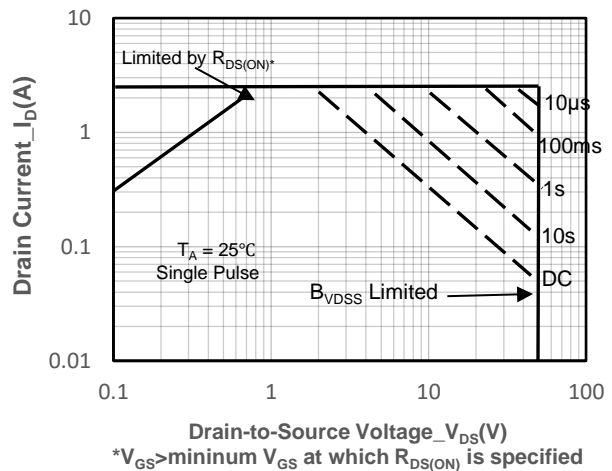
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage

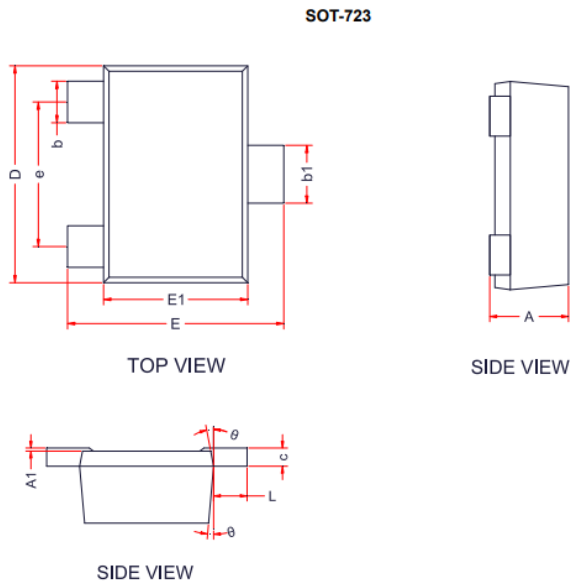


On-Resistance vs. Junction Temperature



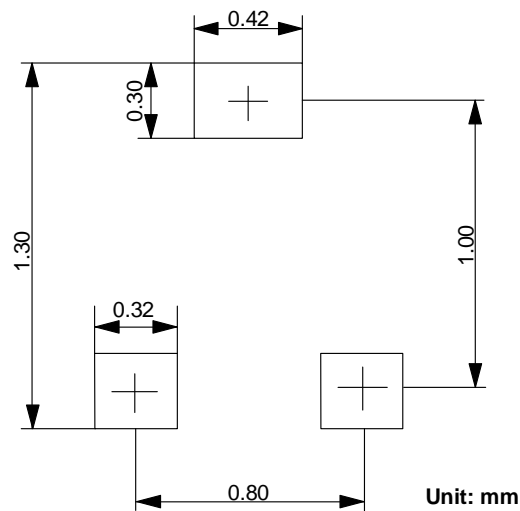
Safe Operating Area vs. Junction-to-Ambient

➤ Package Information



DIM	Millimeters		
	Min.	Typ.	Max.
A	0.43	-	0.55
A1	0.00	-	0.05
b1	0.27		0.37
b	0.17	-	0.27
c	0.08	0.13	0.18
D	1.15	1.20	1.25
E	1.15	1.20	1.25
E1	0.75	0.8	0.85
e	0.80Ref.		
L	0.15	0.2	0.25
θ	7°Ref.		

➤ Suggested Pad Layout





DISCLAIMER

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.